

## Simulation of irradiated silicon p-bulk sensors

*Thursday, November 15, 2012 12:10 PM (20 minutes)*

TCAD simulations of irradiated silicon p-bulk sensors have been carried out and the results have been compared to CERN 24 GeV-p irradiated n-in-p diodes.

The simulations' results are in good agreement with measured data and allow for reliable predictions on future detectors.

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**Session Classification:** Detector Characterization and Simulations

**Track Classification:** RD50/PPS session (Friday morning)